

PLASMA PROCESSING METHOD AND PLASMA PROCESSING APPARATUS

ABSTRACT

The plasma processing method includes process a1),
5 process a2), and process a3). In process a1), the surfaces
of components in a chamber are coated with a conductive
film by turning a first gas and a second gas into plasma in
the chamber. In process a2), the substrate is introduced
into the chamber. In process a3), the substrate is
10 processed by turning a third gas into plasma in the chamber
in a state where the surfaces of components in the chamber
are coated with a conductive film. In addition, the first
gas contains at least one of carbon, silicon and germanium,
and the second gas contains at least one of boron,
15 nitrogen, phosphorus and arsenic.

Figure 2